

# CSD17318Q2 30V N-Channel NexFET™ Power MOSFET

## 1 Features

- Optimized for 5V gate drive
- Low capacitance and charge
- Low  $R_{DS(ON)}$
- Low-thermal resistance
- Lead free
- RoHS compliant
- Halogen free
- SON 2mm × 2mm plastic package

## 2 Applications

- Storage, tablets, and handheld devices
- Optimized for load switch applications
- DC-DC converters
- Battery and load management applications

## 3 Description

This 30V, 12.6mΩ, 2mm × 2mm SON NexFET™ power MOSFET is designed to minimize losses in power conversion applications and optimized for 5V gate drive applications. The 2mm × 2mm SON offers excellent thermal performance for the size of the package.

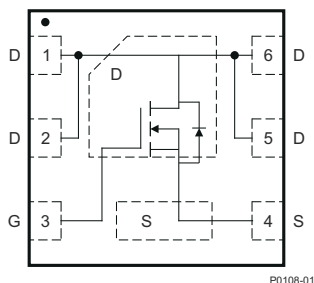
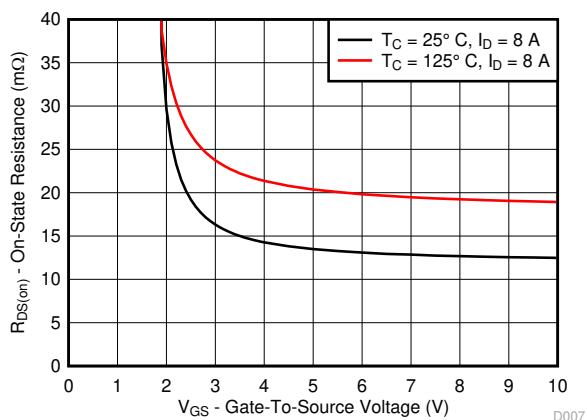


Figure 3-1. Top View



On-State Resistance vs Gate to Source Voltage

## Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE	UNIT
$V_{DS}$	Drain-to-Source Voltage	30	V
$Q_g$	Gate Charge Total (4.5V)	6.0	nC
$Q_{gd}$	Gate Charge Gate-to-Drain	1.3	nC
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 2.5\text{V}$	20
		$V_{GS} = 4.5\text{V}$	13.9
		$V_{GS} = 8\text{V}$	12.6
$V_{GS(th)}$	Threshold Voltage	0.9	V

## Device Information<sup>(1)</sup>

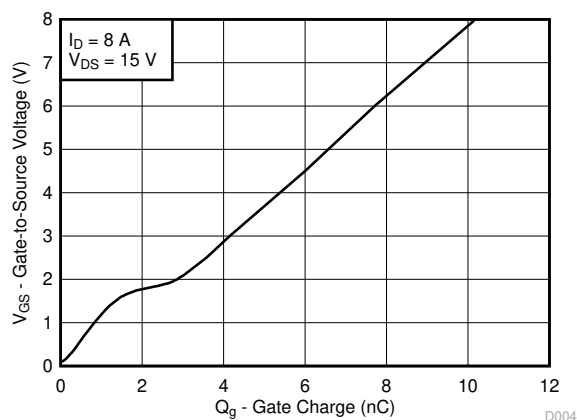
PART NUMBER	QTY	MEDIA	PACKAGE	SHIP
CSD17318Q2	3000	7 Inch Reel	SON	Tape and Reel
CSD17318Q2T	250		2.00mm × 2.00mm Plastic Package	

- (1) For all available packages, see the orderable addendum at the end of the data sheet.

## Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
$V_{DS}$	Drain-to-Source Voltage	30	V
$V_{GS}$	Gate-to-Source Voltage	±10	V
$I_D$	Continuous Drain Current (Package Limited)	21.5	A
	Continuous Drain Current (Silicon Limited), $T_C = 25^\circ\text{C}$	25	
	Continuous Drain Current <sup>(1)</sup>	10	
$I_{DM}$	Pulsed Drain Current, $T_A = 25^\circ\text{C}$ <sup>(2)</sup>	68	A
$P_D$	Power Dissipation <sup>(1)</sup>	2.5	W
	Power Dissipation, $T_C = 25^\circ\text{C}$	16	
$T_J, T_{STG}$	Operating Junction, Storage Temperature	-55 to 150	°C
$E_{AS}$	Avalanche Energy, Single Pulse, $I_D = 12.4\text{A}, L = 0.1\text{mH}, R_G = 25\Omega$	7.7	mJ

- (1) Typical  $R_{\theta JA} = 55^\circ\text{C/W}$  on a 1in<sup>2</sup>, 2oz Cu pad on a 0.06in thick FR4 PCB.  
 (2) Max  $R_{\theta JC} = 7^\circ\text{C/W}$ , pulse duration ≤ 100μs, duty cycle ≤ 1%.



Gate Charge



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## 4 Specifications

### 4.1 Electrical Characteristics

$T_A = 25^\circ\text{C}$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>STATIC CHARACTERISTICS</b>						
$BV_{DSS}$	Drain-to-source voltage	$V_{GS} = 0V, I_D = 250\mu A$	30			V
$I_{DSS}$	Drain-to-source leakage	$V_{GS} = 0V, V_{DS} = 24V$			1	$\mu A$
$I_{GSS}$	Gate-to-source leakage	$V_{DS} = 0V, V_{GS} = 10V$			100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.6	0.9	1.2	V
$R_{DS(on)}$	Drain-to-source on-resistance	$V_{GS} = 2.5V, I_D = 8A$		20	30	m $\Omega$
		$V_{GS} = 4.5V, I_D = 8A$		13.9	16.9	
		$V_{GS} = 8V, I_D = 8A$		12.6	15.1	
$g_{fs}$	Transconductance	$V_{DS} = 3V, I_D = 8A$		42		S
<b>DYNAMIC CHARACTERISTICS</b>						
$C_{iss}$	Input capacitance	$V_{GS} = 0V, V_{DS} = 15V,$ $f = 1MHz$		676	879	pF
$C_{oss}$	Output capacitance			71	92	pF
$C_{riss}$	Reverse transfer capacitance			39	51	pF
$R_G$	Series gate resistance		1.0	2.0		$\Omega$
$Q_g$	Gate charge total (4.5 V)	$V_{DS} = 15V,$ $I_D = 8A$		6.0		nC
$Q_{gd}$	Gate charge gate-to-drain			1.3		nC
$Q_{gs}$	Gate charge gate-to-source			1.5		nC
$Q_{g(th)}$	Gate charge at $V_{th}$			0.7		nC
$Q_{oss}$	Output charge	$V_{DS} = 15V, V_{GS} = 0V$		2.7		nC
$t_{d(on)}$	Turnon delay time	$V_{DS} = 15V, V_{GS} = 4.5V,$ $I_D = 8A, R_G = 2\Omega$		5		ns
$t_r$	Rise time			16		ns
$t_{d(off)}$	Turnoff delay time			13		ns
$t_f$	Fall time			4		ns
<b>DIODE CHARACTERISTICS</b>						
$V_{SD}$	Diode forward voltage	$I_{SD} = 8A, V_{GS} = 0V$	0.8	1.0		V
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 15V, I_F = 8A,$ $di/dt = 300A/\mu s$		2.9		nC
$t_{rr}$	Reverse recovery time			12		ns

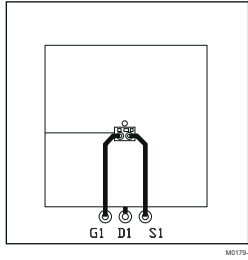
### 4.2 Thermal Characteristics

$T_A = 25^\circ\text{C}$  (unless otherwise noted)

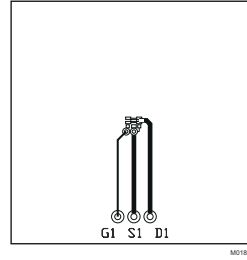
PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal resistance junction-to-case <sup>(1)</sup>			7.9	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal resistance junction-to-ambient <sup>(1) (2)</sup>			65	$^\circ\text{C/W}$

(1)  $R_{\theta JC}$  is determined with the device mounted on a  $1in^2$  ( $6.45cm^2$ ), 2oz (0.071mm) thick Cu pad on a  $1.5in \times 1.5in$  ( $3.81cm \times 3.81cm$ ), 0.06in (1.52mm) thick FR4 PCB.  $R_{\theta JC}$  is specified by design, whereas  $R_{\theta JA}$  is determined by the user's board design.

(2) Device mounted on FR4 material with  $1in^2$  ( $6.45cm^2$ ), 2oz (0.071mm) thick Cu.



Max  $R_{\theta JA} = 65^{\circ}\text{C/W}$  when mounted on  $1\text{in}^2$  ( $6.45\text{cm}^2$ ) of 2oz (0.071mm) thick Cu.



Max  $R_{\theta JA} = 250^{\circ}\text{C/W}$  when mounted on a minimum pad area of 2oz (0.071mm) thick Cu.

### 4.3 Typical MOSFET Characteristics

$T_A = 25^{\circ}\text{C}$  (unless otherwise noted)

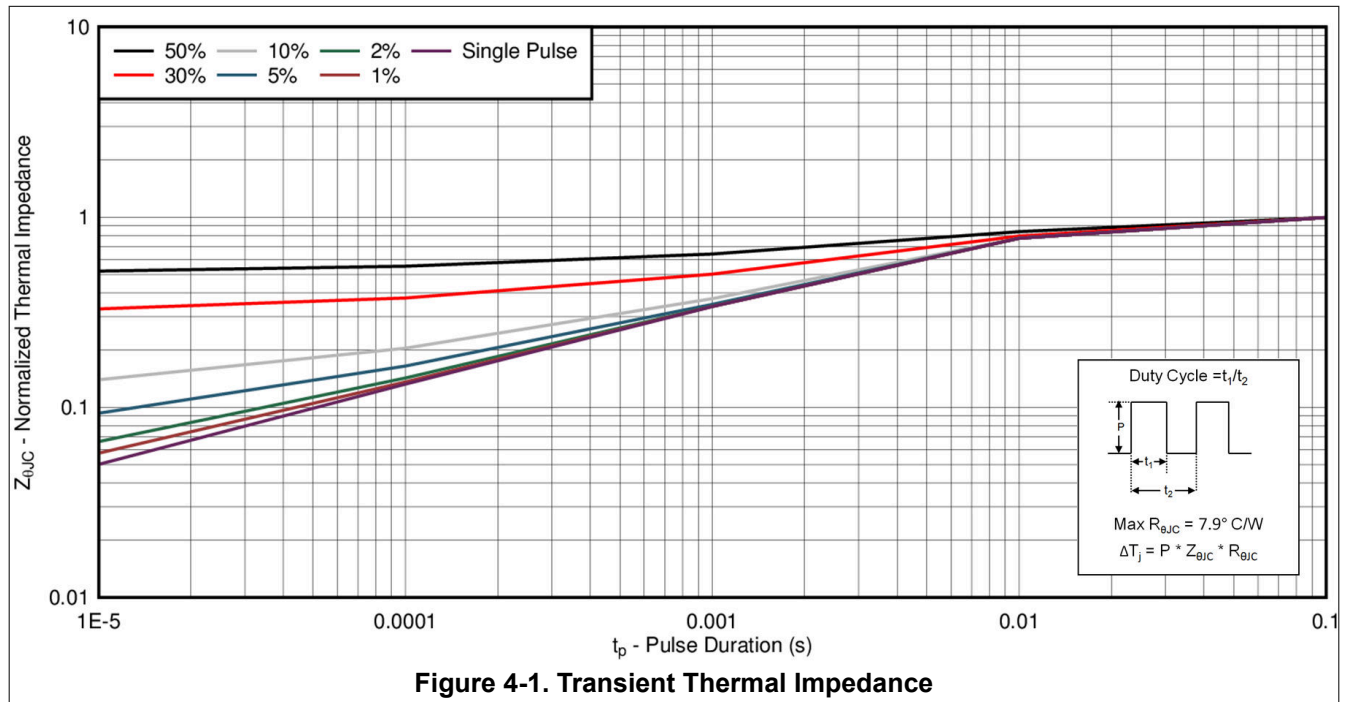


Figure 4-1. Transient Thermal Impedance

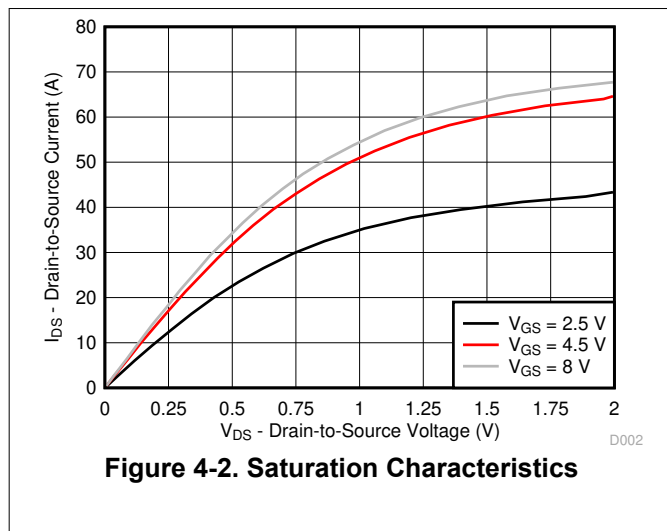


Figure 4-2. Saturation Characteristics

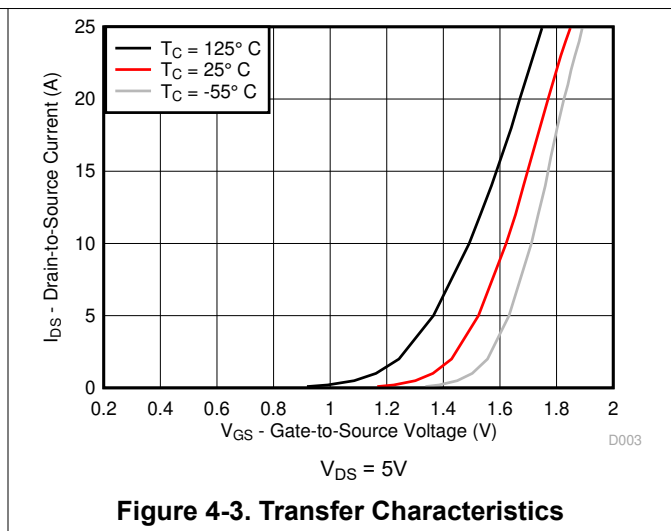


Figure 4-3. Transfer Characteristics

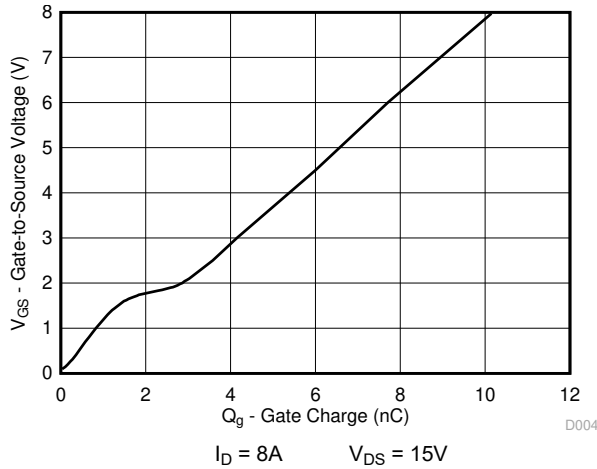


Figure 4-4. Gate Charge

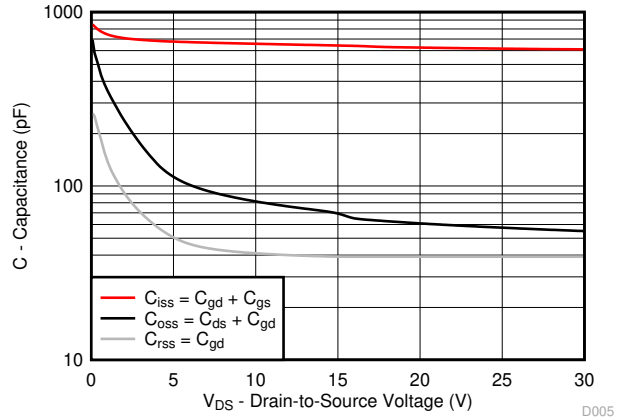


Figure 4-5. Capacitance

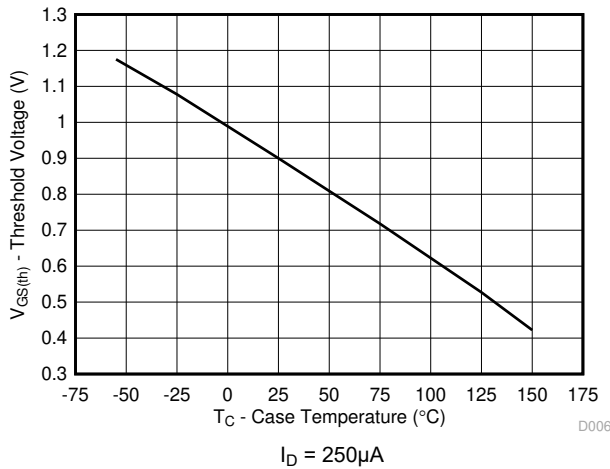


Figure 4-6. Threshold Voltage vs Temperature

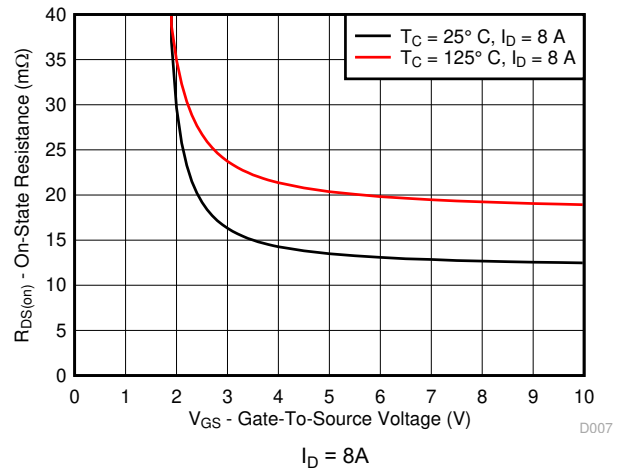


Figure 4-7. On-State Resistance vs Gate-to-Source Voltage

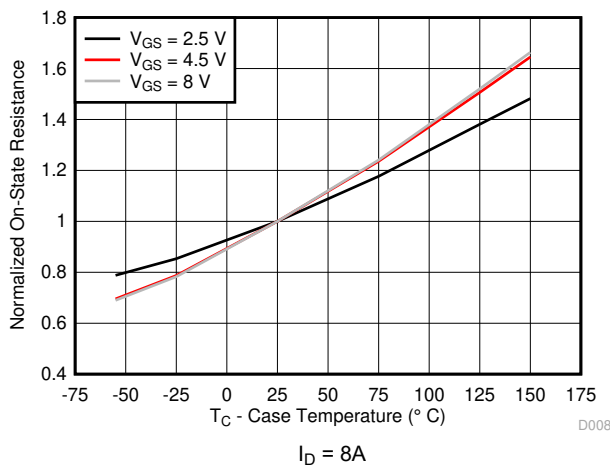


Figure 4-8. Normalized On-State Resistance vs Temperature

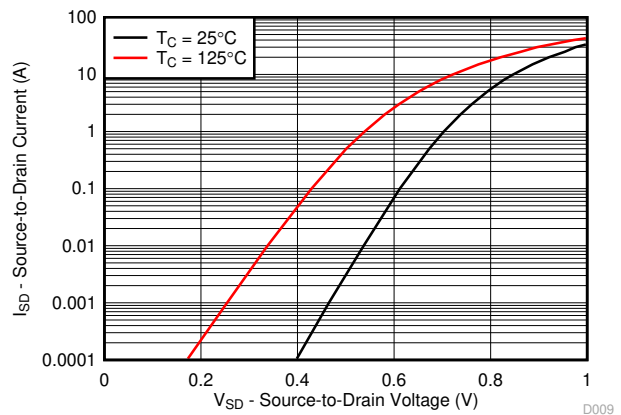
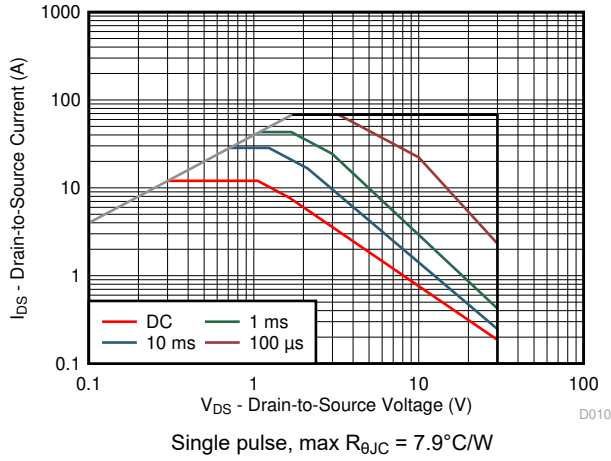
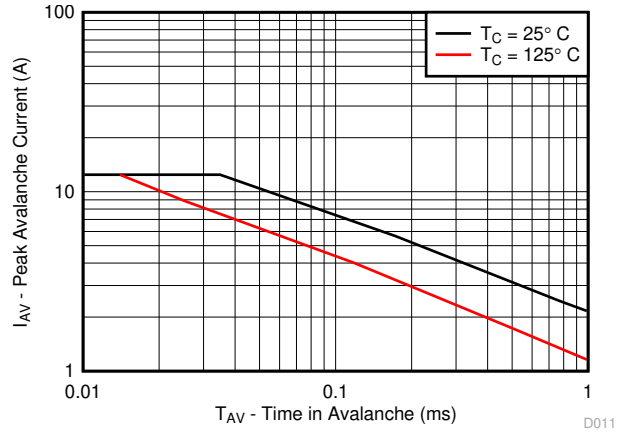


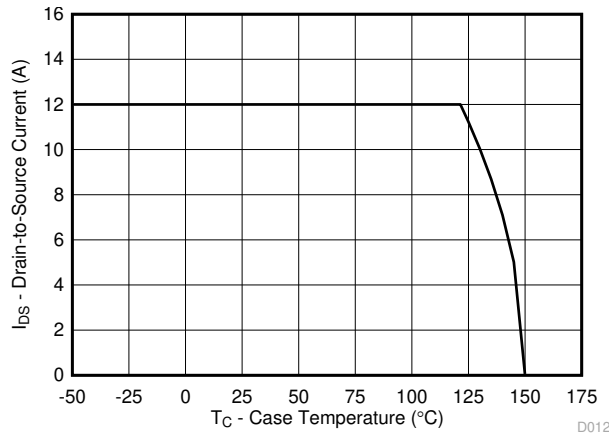
Figure 4-9. Typical Diode Forward Voltage



**Figure 4-10. Maximum Safe Operating Area**



**Figure 4-11. Single Pulse Unclamped Inductive Switching**



**Figure 4-12. Maximum Drain Current vs Temperature**

## 5 Device and Documentation Support

### 5.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](http://ti.com). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 5.2 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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### 5.3 Trademarks

NexFET™ is a trademark of Texas Instruments.

TI E2E™ is a trademark of Texas Instruments.

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## 6 Revision History

<b>Changes from Revision A (February 2017) to Revision B (June 2024)</b>	<b>Page</b>
• Updated the numbering format for tables, figures, and cross-references throughout the document.....	<b>1</b>

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## 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD17318Q2	ACTIVE	WSON	DQK	6	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-55 to 150	1718	<a href="#">Samples</a>
CSD17318Q2T	ACTIVE	WSON	DQK	6	250	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-55 to 150	1718	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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